

Woojin Park

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

48
papers

1,762
citations

21
h-index

41
g-index

53
ext. papers

1,937
ext. citations

5.3
avg, IF

4.14
L-index

#	Paper	IF	Citations
48	The application of graphene as electrodes in electrical and optical devices. <i>Nanotechnology</i> , 2012 , 23, 112001	3.4	265
47	Large-scale patterned multi-layer graphene films as transparent conducting electrodes for GaN light-emitting diodes. <i>Nanotechnology</i> , 2010 , 21, 175201	3.4	233
46	Highly flexible and transparent multilayer MoS ₂ transistors with graphene electrodes. <i>Small</i> , 2013 , 9, 3295-300	11	154
45	Enhanced charge injection in pentacene field-effect transistors with graphene electrodes. <i>Advanced Materials</i> , 2011 , 23, 100-5	24	112
44	Efficient bulk-heterojunction photovoltaic cells with transparent multi-layer graphene electrodes. <i>Organic Electronics</i> , 2010 , 11, 1864-1869	3.5	106
43	Tuning of a graphene-electrode work function to enhance the efficiency of organic bulk heterojunction photovoltaic cells with an inverted structure. <i>Applied Physics Letters</i> , 2010 , 97, 213301	3.4	87
42	Tuning of the electronic characteristics of ZnO nanowire field effect transistors by proton irradiation. <i>ACS Nano</i> , 2010 , 4, 811-8	16.7	56
41	Enhancement in the photodetection of ZnO nanowires by introducing surface-roughness-induced traps. <i>Nanotechnology</i> , 2011 , 22, 205204	3.4	46
40	Thermal stability of multilayer graphene films synthesized by chemical vapor deposition and stained by metallic impurities. <i>Nanotechnology</i> , 2012 , 23, 075702	3.4	45
39	Diameter-engineered SnO ₂ nanowires over contact-printed gold nanodots using size-controlled carbon nanopost array stamps. <i>ACS Nano</i> , 2010 , 4, 1829-36	16.7	45
38	Au nanoparticle-decorated graphene electrodes for GaN-based optoelectronic devices. <i>Applied Physics Letters</i> , 2012 , 101, 031115	3.4	42
37	Enhanced Performance of MoS Photodetectors by Inserting an ALD-Processed TiO Interlayer. <i>Small</i> , 2018 , 14, 1703176	11	39
36	Nonvolatile memory functionality of ZnO nanowire transistors controlled by mobile protons. <i>ACS Nano</i> , 2011 , 5, 558-64	16.7	38
35	Characteristics of a pressure sensitive touch sensor using a piezoelectric PVDF-TrFE/MoS ₂ stack. <i>Nanotechnology</i> , 2013 , 24, 475501	3.4	34
34	Logic inverters composed of controlled depletion-mode and enhancement-mode ZnO nanowire transistors. <i>Applied Physics Letters</i> , 2009 , 94, 173118	3.4	31
33	Modulation of Synaptic Plasticity Mimicked in Al Nanoparticle-Embedded IGZO Synaptic Transistor. <i>Advanced Electronic Materials</i> , 2020 , 6, 1901072	6.4	27
32	Electrical properties of ZnO nanowire field effect transistors with varying high-k Al ₂ O ₃ dielectric thickness. <i>Journal of Applied Physics</i> , 2010 , 107, 034504	2.5	24

31	A study of graphene films synthesized on nickel substrates: existence and origin of small-base-area peaks. <i>Nanotechnology</i> , 2011 , 22, 045706	3-4	24
30	Enhanced characteristics of pentacene field-effect transistors with graphene electrodes and substrate treatments. <i>Applied Physics Letters</i> , 2011 , 99, 083306	3-4	23
29	Complementary Unipolar WS ₂ Field-Effect Transistors Using Fermi-Level Depinning Layers. <i>Advanced Electronic Materials</i> , 2016 , 2, 1500278	6.4	22
28	Transient drain current characteristics of ZnO nanowire field effect transistors. <i>Applied Physics Letters</i> , 2009 , 95, 123101	3-4	21
27	Highly sensitive wide bandwidth photodetectors using chemical vapor deposited graphene. <i>Applied Physics Letters</i> , 2014 , 104, 161902	3-4	19
26	Tuning of operation mode of ZnO nanowire field effect transistors by solvent-driven surface treatment. <i>Nanotechnology</i> , 2009 , 20, 475702	3-4	19
25	Contact Resistance Reduction of WS ₂ FETs Using High-Pressure Hydrogen Annealing. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 164-168	2-3	17
24	Low Power MoS ₂ /Nb ₂ O ₅ Memtransistor Device with Highly Reliable Heterosynaptic Plasticity. <i>Advanced Functional Materials</i> , 2021 , 31, 2104174	15.6	15
23	Patterned catalyst arrays of Pd/SnO ₂ core-shell nanowires for electrooxidations of biomass-derived alcohols. <i>Journal of Materials Chemistry A</i> , 2015 , 3, 13492-13499	13	13
22	Novel Exfoliation of High-Quality 2H-MoS Nanoflakes for Solution-Processed Photodetector. <i>Nanomaterials</i> , 2020 , 10,	5-4	12
21	Investigation of threshold voltage instability induced by gate bias stress in ZnO nanowire field effect transistors. <i>Nanotechnology</i> , 2012 , 23, 485201	3-4	11
20	Stable MoS ₂ Field-Effect Transistors Using TiO ₂ Interfacial Layer at Metal/MoS ₂ Contact. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700534	1.6	10
19	Characteristics of light-induced electron transport from P3HT to ZnO-nanowire field-effect transistors. <i>Applied Physics Letters</i> , 2013 , 103, 223305	3-4	9
18	Reduction of low-frequency noise in multilayer MoS ₂ FETs using a Fermi-level depinning layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016 , 10, 634-638	2.5	9
17	Highly Stable and Ultrafast Hydrogen Gas Sensor Based on 15 nm Nanogaps Switching in a Palladium-Gold Nanoribbons Array. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1801442	4.6	9
16	Al ₂ O ₃ -Induced Sub-Gap Doping on the IGZO Channel for the Detection of Infrared Light. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 1478-1483	4	8
15	Improvement of the Bias Stress Stability in 2D MoS and WS Transistors with a TiO Interfacial Layer. <i>Nanomaterials</i> , 2019 , 9,	5-4	6
14	Enhanced Photoresponse of WS ₂ Photodetectors through Interfacial Defect Engineering Using a TiO ₂ Interlayer. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 838-845	4	6

13	In-Line Tunnel Field Effect Transistor: Drive Current Improvement. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 721-725	2.3	5
12	UV photoconductivity characteristics of ZnO nanowire field effect transistor treated by proton irradiation. <i>Thin Solid Films</i> , 2012 , 520, 3624-3628	2.2	4
11	Artificial 2D van der Waals Synapse Devices via Interfacial Engineering for Neuromorphic Systems. <i>Nanomaterials</i> , 2020 , 10,	5.4	4
10	One-step HS reactive sputtering for 2D MoS/Si heterojunction photodetector. <i>Nanotechnology</i> , 2020 , 31, 225205	3.4	3
9	Proton Irradiation-Induced Electrostatic Modulation in ZnO Nanowire Field-Effect Transistors With Bilayer Gate Dielectric. <i>IEEE Nanotechnology Magazine</i> , 2012 , 11, 918-923	2.6	3
8	Contact resistance reduction of ZnO thin film transistors (TFTs) with saw-shaped electrode. <i>Nanotechnology</i> , 2018 , 29, 325202	3.4	3
7	Facile fabrication of ZnO nanowire memory device based on chemically-treated surface defects. <i>Nanotechnology</i> , 2019 , 30, 155201	3.4	2
6	Photonics: Enhanced Performance of MoS ₂ Photodetectors by Inserting an ALD-Processed TiO ₂ Interlayer (Small 5/2018). <i>Small</i> , 2018 , 14, 1870022	1.1	2
5	Characterization on Improved Effective Mobility of Pentacene Organic Field-Effect Transistors Using Graphene Electrodes. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 02BK09	1.4	2
4	Characterization on Improved Effective Mobility of Pentacene Organic Field-Effect Transistors Using Graphene Electrodes. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 02BK09	1.4	2
3	Characterization of ZnO Nanowire Field Effect Transistors by Fast Hydrogen Peroxide Solution Treatment. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 035001	1.4	1
2	Unveiling the Role of Al ₂ O ₃ Interlayer in IndiumGalliumZincOxide Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000621	1.6	1
1	Characterization of ZnO Nanowire Field Effect Transistors by Fast Hydrogen Peroxide Solution Treatment. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 035001	1.4	